

Features

- Low gate charge
- 100% avalanche tested
- Improved dv/dt capability
- RoHS compliant
- Halogen free package
- JEDEC Qualification

 $V_{DSS} = 990 \text{ V} @ T_{jmax}$ $I_D = 9 \text{ A}$ $R_{DS(ON)} = 1.4 \Omega(\text{max}) @ V_{GS} = 10 \text{ V}$ **Absolute Maximum Ratings**

Parameter	Symbol	TMP9N90(G)	TMPF9N90(G)	Unit
Drain-Source Voltage	V_{DSS}	900		V
Gate-Source Voltage	V_{GS}	± 30		V
Continuous Drain Current	I_D	9	9 *	A
		5.7	5.7 *	A
Pulsed Drain Current ^(Note 1)	I_{DM}	36	36*	A
Single Pulse Avalanche Energy ^(Note 2)	E_{AS}	221		mJ
Repetitive Avalanche Current ^(Note 1)	I_{AR}	9		A
Repetitive Avalanche Energy ^(Note 1)	E_{AR}	29		mJ
Power Dissipation	P_D	290	48	W
		2.32	0.38	W/°C
Peak Diode Recovery dv				

Electrical Characteristics : $T_c=25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Test condition	Min	Typ	Max	Units
OFF						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{\text{GS}} = 0 \text{ V}, I_{\text{D}} = 250 \mu\text{A}$	900	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{\text{DS}} = 900 \text{ V}, V_{\text{GS}} = 0 \text{ V}$	--	--	10	μA
		$V_{\text{DS}} = 720 \text{ V}, T_c = 125^\circ\text{C}$	--	--	100	μA
Forward Gate-Source Leakage Current	I_{GSSF}	$V_{\text{GS}} = 30 \text{ V}, V_{\text{DS}} = 0 \text{ V}$	--	--	100	nA
Reverse Gate-Source Leakage Current	I_{GSSR}	$V_{\text{GS}} = -30 \text{ V}, V_{\text{DS}} = 0 \text{ V}$	--	--	-100	nA
ON						
Gate Threshold Voltage	$V_{\text{GS(th)}}$	$V_{\text{DS}} = V_{\text{GS}}, I_{\text{D}} = 250 \mu\text{A}$	2	--	4	V
Drain-Source On-Resistance	$R_{\text{DS(on)}}$	$V_{\text{GS}} = 10 \text{ V}, I_{\text{D}} = 4.5 \text{ A}$	--	1.13	1.4	Ω
Forward Transconductance ^(Note 4)	g_{FS}	$V_{\text{DS}} = 30 \text{ V}, I_{\text{D}} = 4.5 \text{ A}$	--	10	--	S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 25 \text{ V}, V_{\text{GS}} = 0 \text{ V}, f = 1.0 \text{ MHz}$	--	2324	--	pF
Output Capacitance	C_{oss}		--	184	--	pF
Reverse Transfer Capacitance	C_{rss}		--	29	--	pF
SWITCHING						
Turn-On Delay Time ^(Note 4,5)	$t_{\text{d(on)}}$	$V_{\text{DD}} = 450 \text{ V}, I_{\text{D}} = 9 \text{ A}, R_{\text{G}} = 25$	--	61	--	ns
Turn-On Rise Time ^(Note 4,5)	t_r		--	49	--	ns
Turn-Off Delay Time ^(Note 4,5)	$t_{\text{d(off)}}$		--	318	--	ns
Turn-Off Fall Time ^(Note 4,5)						

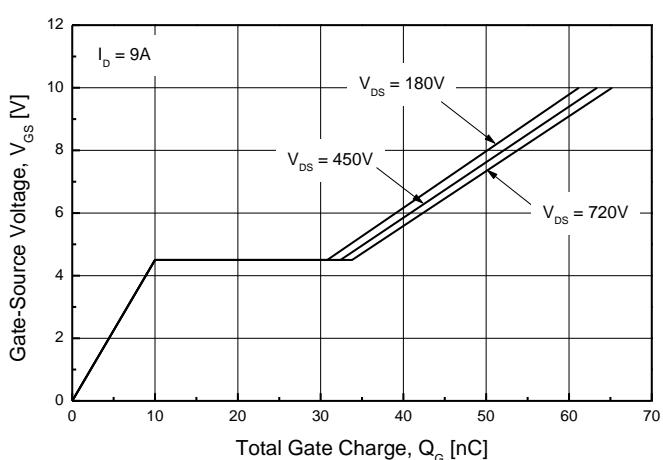
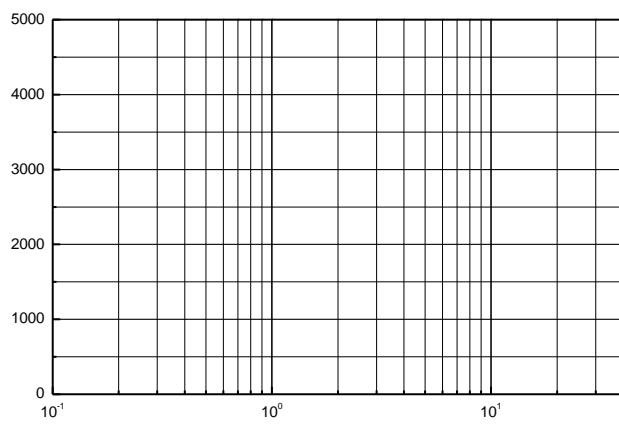
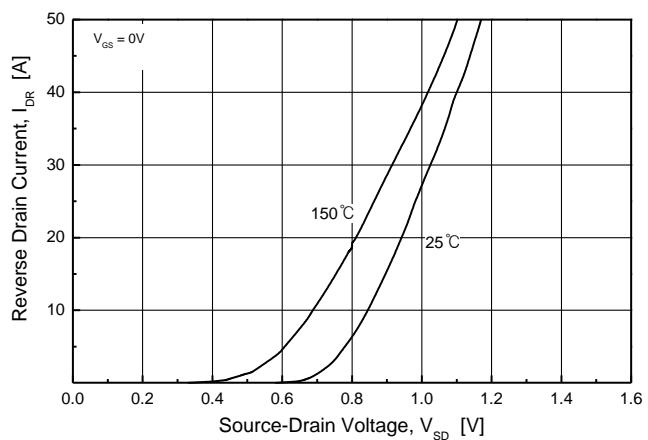
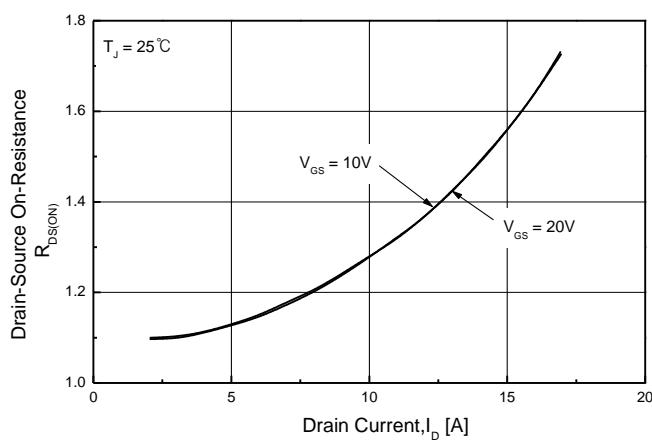
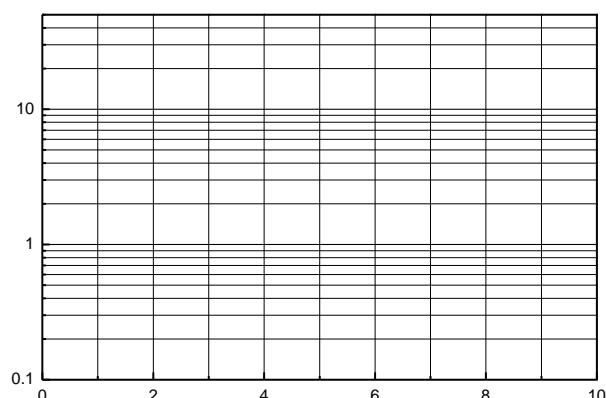
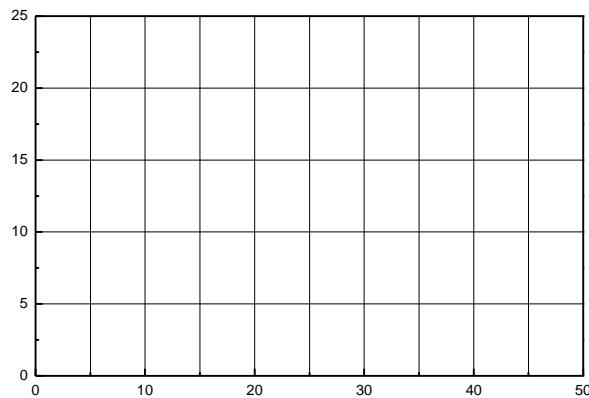
Note :

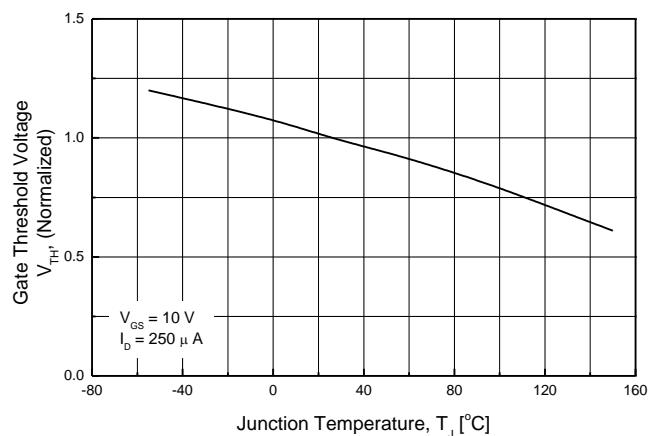
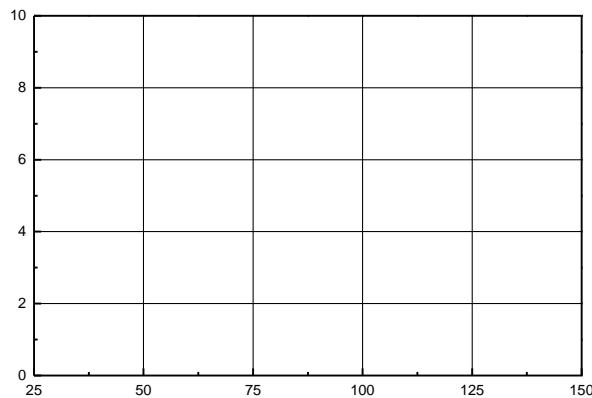
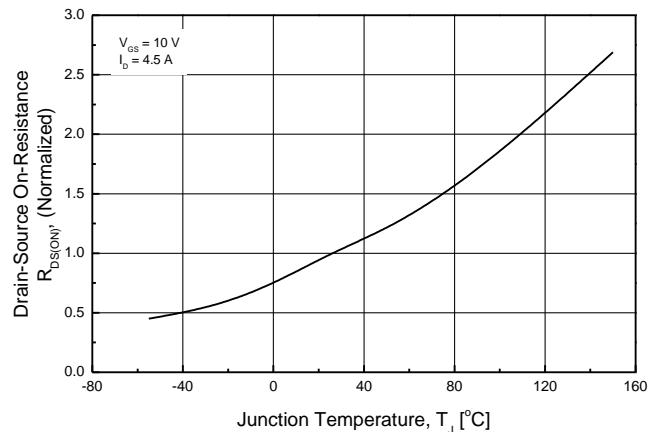
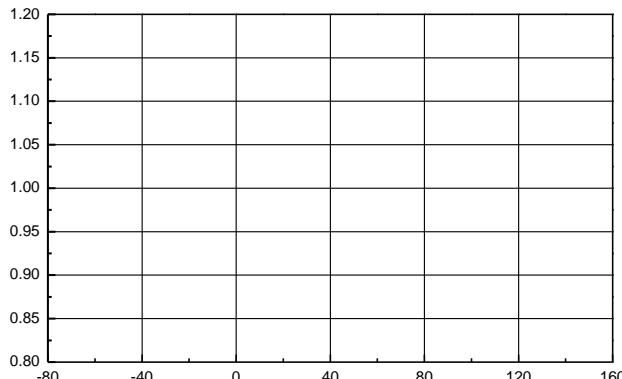
1. Repeated rating : Pulse width limited by safe operating area

2. $L=5.16\text{mH}$, $I_{\text{AS}} = 9\text{A}$, $V_{\text{DD}} = 50\text{V}$, $R_{\text{G}} = 25$, Starting $T_j = 25^\circ\text{C}$

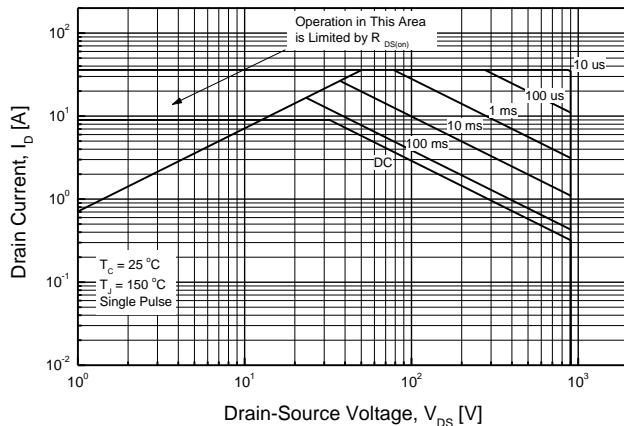
3 I_{SD} di/dt μs , V_{DD} V_{DS} , Starting $T_j = 25^\circ\text{C}$

5. Essentially Independent of Operating Temperature Typical Characteristics

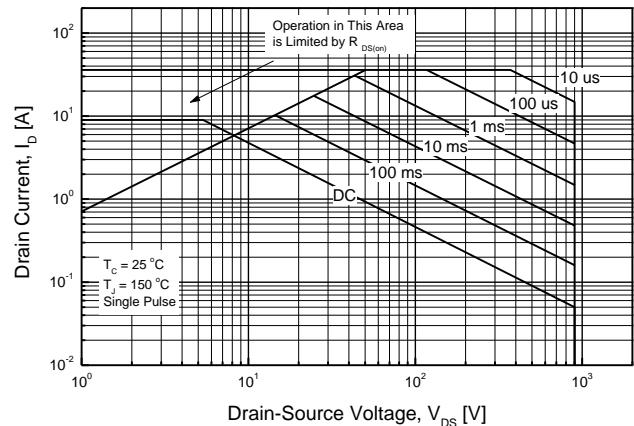


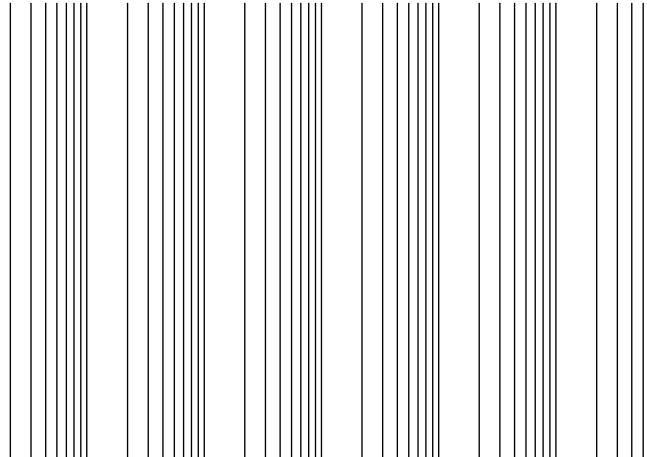


TMP9N90(G)



TMPF9N90(G)



TMP9N90(G)**TMPF9N90(G)**